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45 V/60 V/80 V, 1 A PNP medium power transistors

Rev. 1 — 19 June 2015

Produ

Product data sheet

Product profile

1.1 General description

PNP medium power transistor series encapsulated in an ultra thin DFN2020D-3 (SOT1061D) leadless small Surface-Mounted Device (SMD) plastic package with medium power capability and visible and solderable side pads.

Table 1. **Product overview**

Type number[1]	Package	Package	
BC51PAS	DFN2020D-3	SOT1061D	BC54PAS
BC52PAS			BC55PAS
BC53PAS			BC56PAS

[1] Valid for all available selection groups.

1.2 Features and benefits

- High collector current capability I_C and I_{CM}
- Reduced Printed-Circuit Board (PCB) area requirements
- Exposed heat sink for excellent thermal and electrical conductivity
- AEC-Q101 qualified

- Three current gain selections
- Leadless very small SMD plastic package with medium power capability
- Suitable for Automatic Optical Inspection (AOI) of solder joint

1.3 Applications

- Linear voltage regulators
- Battery driven devices
- MOSFET drivers

- High-side switches
- Power management
- Amplifiers

1.4 Quick reference data

Quick reference data Table 2.

T_{amb} = 25 °C unless otherwise specified

· anno =0						
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base				
	BC51PAS series		-	-	-45	V
	BC52PAS series		-	-	-60	V
	BC53PAS series		-	-	-80	٧



45 V/60 V/80 V, 1 A PNP medium power transistors

Table 2. Quick reference data ...continued

T_{amb} = 25 °C unless otherwise specified

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _C	collector current			-	-	-1	Α
I _{CM}	peak collector current	single pulse; $t_p \le 1$ ms		-	-	-2	Α
h _{FE}	DC current gain	$V_{CE} = -2 \text{ V}; I_{C} = -150 \text{ mA}$	[1]	63	-	250	
	h _{FE} selection -10	$V_{CE} = -2 \text{ V}; I_{C} = -150 \text{ mA}$	[1]	63	-	160	
	h _{FE} selection -16	$V_{CE} = -2 \text{ V}; I_{C} = -150 \text{ mA}$	[1]	100	-	250	

^[1] Pulse test: $t_p \le 300$ ms; $\delta \le 0.02$.

2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	base		_
2	emitter	3	3
3	collector	Transparent top view	1

3. Ordering information

Table 4. Ordering information

Type number[1]	Package				
	Name	Description	Version		
BC51PAS series	DFN2020D-3	plastic thermal enhanced ultra thin small	SOT1061D		
BC52PAS series		outline package; no leads; 3 terminals; body $2 \times 2 \times 0.65$ mm.			
BC53PAS series		body 2 × 2 × 0.05 mm.			

^[1] Valid for all available selection groups.

4. Marking

Table 5. Marking codes

Type number	Marking code
BC51PAS	C4
BC51-10PAS	C5
BC51-16PAS	C6
BC52PAS	C7
BC52-10PAS	C8
BC52-16PAS	C9
BC53PAS	CA
BC53-10PAS	СВ
BC53-16PAS	CC

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter			
	BC51PAS series		-	-45	V
	BC52PAS series		-	-60	V
	BC53PAS series		-	-100	V
V_{CEO}	collector-emitter voltage	open base			
	BC51PAS series		-	-45	V
	BC52PAS series		-	-60	V
	BC53PAS series		-	-80	V
V_{EBO}	emitter-base voltage	open collector	-	-5	V
Ic	collector current		-	-1	Α
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-2	Α
I _B	base current		-	-0.3	Α

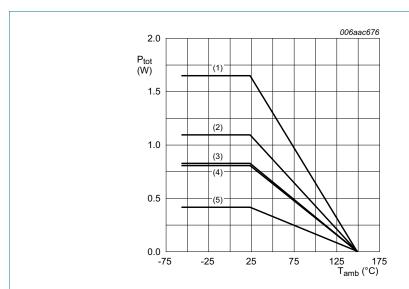
45 V/60 V/80 V, 1 A PNP medium power transistors

Table 6. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.42	W
			[2]	-	0.81	W
			[3]	-	0.83	W
			[4]	-	1.10	W
			[5]	-	1.65	W
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			- 65	150	°C

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 1 cm².
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 cm².
- [5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and mounting pad for collector 1 cm².



- (1) FR4 PCB, 4-layer copper, 1 cm²
- (2) FR4 PCB, single-sided copper, 6 cm²
- (3) FR4 PCB, single-sided copper, 1 cm²
- (4) FR4 PCB, 4-layer copper, standard footprint
- (5) FR4 PCB, single-sided copper, standard footprint

Fig 1. Power derating curves

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions		Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	298	K/W
			[2]	154	K/W
			[3]	151	K/W
			[4]	114	K/W
			[5]	76	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point	in free air		20	K/W

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 1 cm².
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 cm².
- [5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and mounting pad for collector 1 cm²

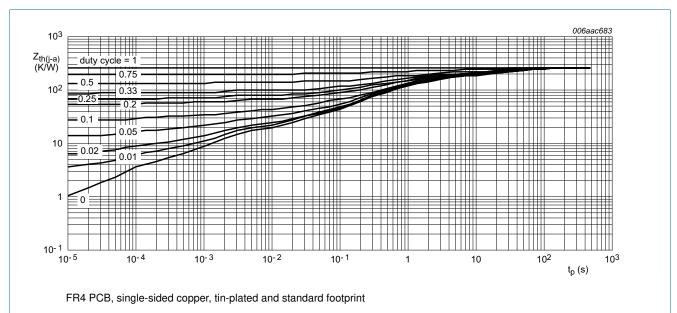
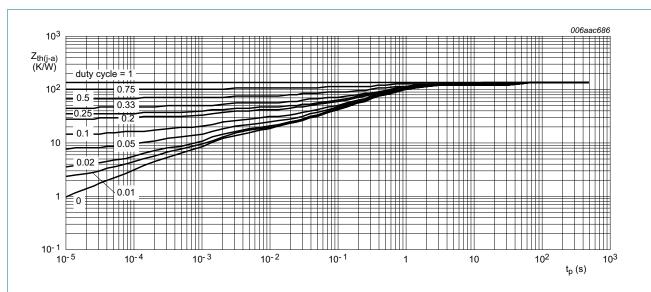
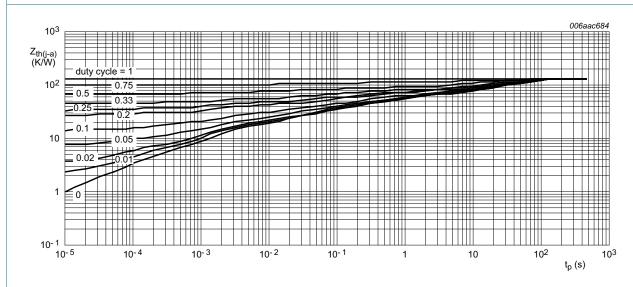


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for; typical values



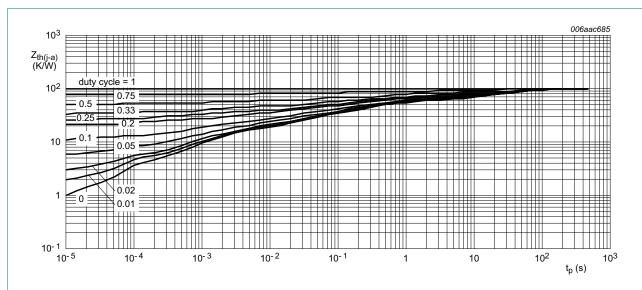
FR4 PCB, 4-layer copper, tin-plated and standard footprint.

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for; typical values



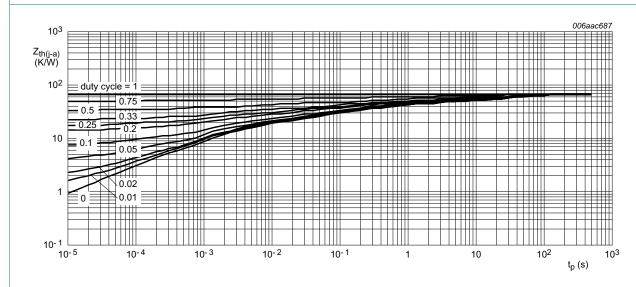
FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 1 cm²

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration for; typical values



FR4 PCB, single-sided copper, tin-plated and mounting pad for collector 6 cm²

Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration for; typical values



FR4 PCB, 4-layer copper, tin-plated and mounting pad for collector 1 cm²

Fig 6. Transient thermal impedance from junction to ambient as a function of pulse duration for; typical values

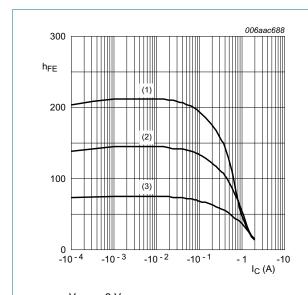
7. Characteristics

Table 8. Characteristics

T_{amb} = 25 °C unless otherwise specified

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off current	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}$		-	-	-100	nA
		$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}; T_j = 150 \text{ °C}$		-	-	-10	μА
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_{C} = 0 \text{ A}$		-	-	-100	nA
h _{FE}	DC current gain	$V_{CE} = -2 \text{ V}; I_{C} = -5 \text{ mA}$		63	-	-	
		$V_{CE} = -2 \text{ V}; I_{C} = -150 \text{ mA}$	[1]	63	-	250	
		$V_{CE} = -2 \text{ V}; I_{C} = -500 \text{ mA}$	[1]	40	-	-	
	h _{FE} selection -10	$V_{CE} = -2 \text{ V}; I_{C} = -150 \text{ mA}$	[1]	63	-	160	
	h _{FE} selection -16	$V_{CE} = -2 \text{ V}; I_{C} = -150 \text{ mA}$	[1]	100	-	250	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}$	[1]	-	-	-500	mV
V_{BE}	base-emitter voltage	$V_{CE} = -2 \text{ V}; I_{C} = -500 \text{ mA}$	[1]	-	-	-1	V
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A}; f = 1 \text{ MHz}$		-	15	-	pF
f _T	transition frequency	$V_{CE} = -5 \text{ V}; I_{C} = -50 \text{ mA}; f = 100 \text{ MHz}$		-	145	-	MHz

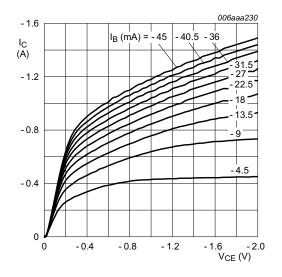
[1] Pulse test: $t_p \le 300$ ms; $\delta \le 0.02$.





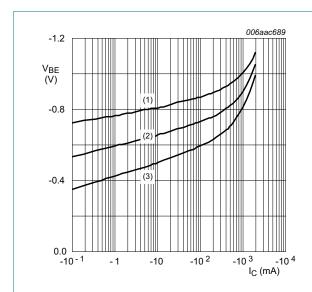
- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

Fig 7. DC current gain as a function of collector current; typical values



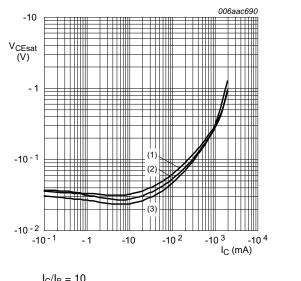
 $T_{amb} = 25 \, ^{\circ}C$

Fig 8. Collector current as a function of collector-emitter voltage; typical values



- $V_{CE} = -2 V$
- (1) $T_{amb} = -55 \,^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 100 \, ^{\circ}C$

Base-emitter voltage as a function of collector current; typical values



- $I_{\rm C}/I_{\rm B} = 10$
- (1) $T_{amb} = 100 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

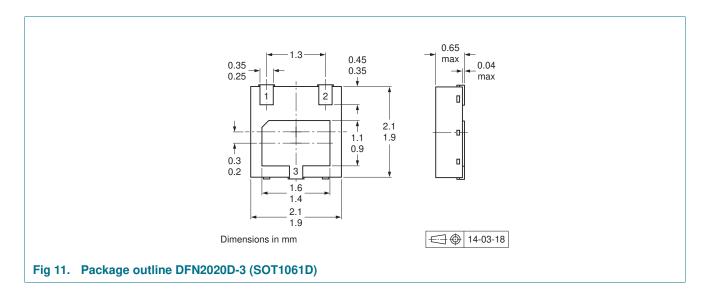
Fig 10. Collector-emitter saturation voltage as a function of collector current; typical values

Test information 8.

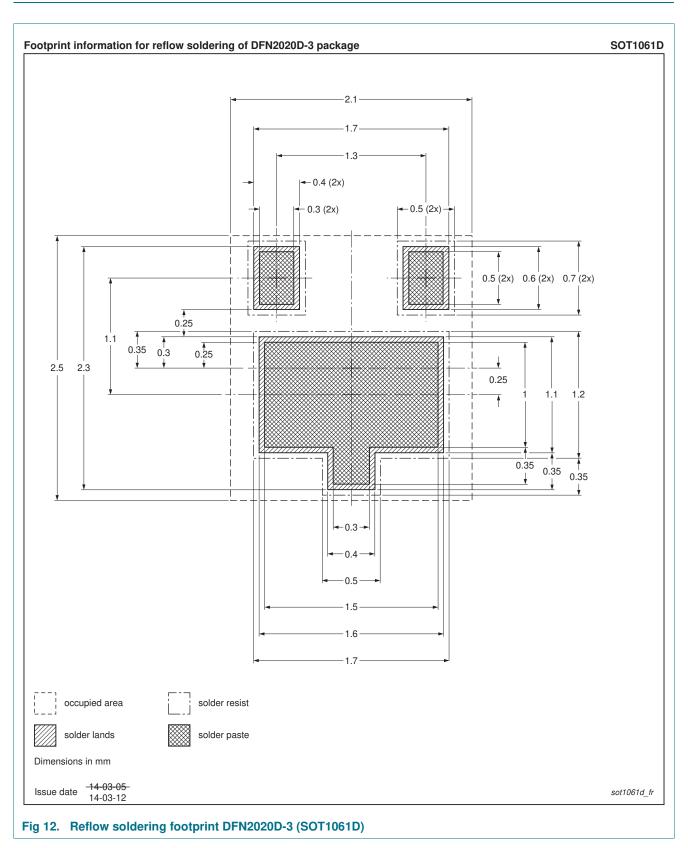
Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

9. Package outline



10. Soldering



BC51_52_53PAS_SER

45 V/60 V/80 V, 1 A PNP medium power transistors

11. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BC51_52_53PAS_SER v.1	20150619	Product data sheet	-	-

45 V/60 V/80 V, 1 A PNP medium power transistors

12. Legal information

12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
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BC51_52_53PAS_SER

45 V/60 V/80 V, 1 A PNP medium power transistors

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NXP Semiconductors

BC51PAS; BC52PAS; BC53PAS

45 V/60 V/80 V, 1 A PNP medium power transistors

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